

IN THE SPECIFICATION:

Please amend Table 26 on page 80, beginning at line 9 and ending at line 41, as follows.

(Table 26)

	<u>Lower=</u> <u>part</u> <u>block-</u> <u>ing</u> <u>layer</u>	<u>Photoconductive</u> <u>layer</u> <u>Photo-</u> <u>conduc-</u> <u>tive</u> <u>layer</u> <u>region</u>	<u>Photo-</u> <u>conduc-</u> <u>tive</u> <u>layer</u> <u>region</u>	<u>Surface</u> <u>layer</u>
Source gases and flow rates:				
SiH ₄ [ml/min(normal)]	100	250	150	250→30→12
H ₂ [ml/min(normal)]	700	2,000	600	-
B ₂ H ₆ (ppm) (based on SiH ₄)	1,500	0.1	-	-
NO [ml/min(normal)]	10	-	-	-
CH ₄ [ml/min(normal)]	-	-	-	5→60→600
Substrate temperature: (°C)	290	280	260	240
Reactor internal pressure: (Pa)	55	60	58	44
High-frequency power: (W) (13.56 MHz)	150	600	150	400
Layer thickness: (μm)	4	10 ±2 (twice)	10 (once)	0.6